

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claim 1 (currently amended): A semiconductor power module, comprising:

a lead frame having a first portion at a first level, a second portion surrounding the first portion at a second level, and a plurality of terminals connected to the second portion;

a power circuit mounted on a first surface of the first portion;

a heat sink having an electrically insulating property and thermal conductivity, wherein the heat sink directly contacts a second surface opposite the first surface of the first portion of the lead frame; and

a sealer having an electrically insulating property that covers the power circuit.

Claim 2 (original): The semiconductor power module of claim 1, wherein the first portion of the lead frame is centrally positioned within the lead frame.

Claim 3 (original): The semiconductor power module of claim 1, wherein the power circuit includes a power semiconductor element.

Claim 4 (original): The semiconductor power module of claim 1, wherein the first surface of the first portion is a top surface and wherein the second surface of the first portion is a bottom surface.

Claim 5 (original): The semiconductor power module of claim 1, further comprising a control circuit that drives the power circuit.

Claim 6 (original): The semiconductor power module of claim 1, further comprising a heat detection circuit that detects the heat produced by the power circuit.

Claim 7 (cancelled).

Claim 8 (previously presented): The semiconductor power module of claim 1, wherein the heat sink is adhered to at least one of the lead frame and the sealer with an adhesive.

Claim 9 (original): The semiconductor power module of claim 8, wherein the adhesive contains a filler that includes at least one compound selected from the group consisting of  $\text{Al}_2\text{O}_3$ ,  $\text{AlN}$  and  $\text{BeO}$ .

Claim 10 (previously presented): The semiconductor power module of claim 1, wherein the heat sink and the sealer each have grooves or rings and wherein the heat sink and the sealer are connected to each other by means of the grooves or the rings.

Claim 11 (previously presented): The semiconductor power module of claim 1, wherein the heat sink is sheet-shaped and comprises at least one compound selected from the group consisting of  $\text{Al}_2\text{O}_3$ ,  $\text{AlN}$  and  $\text{BeO}$ .

Claim 12 (withdrawn): A method of manufacturing a semiconductor power module having a lead frame with a first portion at a first level and a second portion surrounding the first portion at a second level, the method comprising the steps of:

- die-bonding a power circuit onto a first surface of the first portion of the lead frame;
- wire bonding electrodes of the power circuit to the lead frame;
- molding the lead frame and the power circuit with a sealer; and
- adhering an insulator with thermal conductivity and an electrically insulating property onto a second surface of the first portion.

Claim 13 (withdrawn): The method of claim 12, further comprising the step of die-bonding a heat detection circuit onto the lead frame.

Claim 14 (withdrawn): The method of claim 12, wherein the step of adhering the insulator onto the second surface of the first portion includes the step of adhering the insulator directly to the first portion of the lead frame.

Claim 15 (withdrawn): The method of claim 12, comprising the step of adhering the insulator onto the second surface of the first portion with an adhesive.

Claim 16 (withdrawn): The method of claim 15, wherein the adhesive contains at least one compound selected from the group consisting of  $\text{Al}_2\text{O}_3$ ,  $\text{AlN}$  and  $\text{BeO}$ .

Claim 17 (withdrawn): The method of claim 12, wherein the insulator and the sealer each have grooves or rings and wherein the insulator and the sealer are connected to each other by means of the grooves or the rings.

Claim 18 (withdrawn): The method of claim 12, wherein the insulator is sheet-shaped and comprises at least one compound selected from the group consisting of  $\text{Al}_2\text{O}_3$ ,  $\text{AlN}$ , and  $\text{BeO}$ .